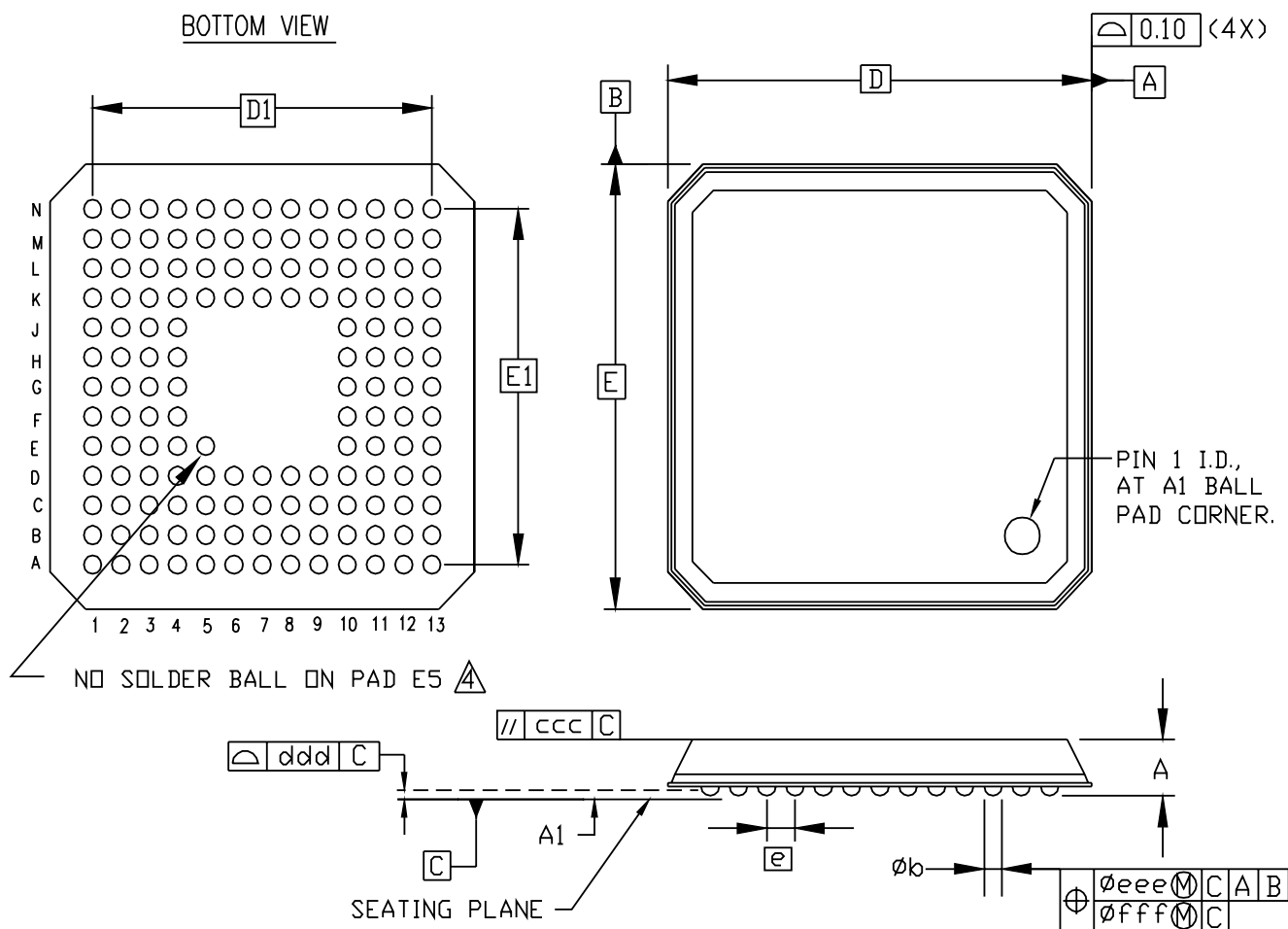

Package Specifications

This section contains specifications for the following Virtex-II packages:

- "CS144 Chip-Scale BGA Package (0.80 mm Pitch)" on page 451
- "FG256 Fine-Pitch BGA Package (1.00 mm Pitch)" on page 452
- "FG456 Fine-Pitch BGA Package (1.00 mm Pitch)" on page 453
- "FG676 Fine-Pitch BGA Package (1.00 mm Pitch)" on page 454
- "BG575 Standard BGA Package (1.27 mm Pitch)" on page 455
- "BG728 Standard BGA Package (1.27 mm Pitch)" on page 456
- "FF896 Flip-Chip Fine-Pitch BGA Package (1.00 mm Pitch)" on page 457
- "FF1152 Flip-Chip Fine-Pitch BGA Package (1.00 mm Pitch)" on page 458
- "FF1517 Flip-Chip Fine-Pitch BGA Package (1.00 mm Pitch)" on page 459
- "BF957 Flip-Chip BGA Package (1.27 mm Pitch)" on page 460

CS144 Chip-Scale BGA Package (0.80 mm Pitch)



4

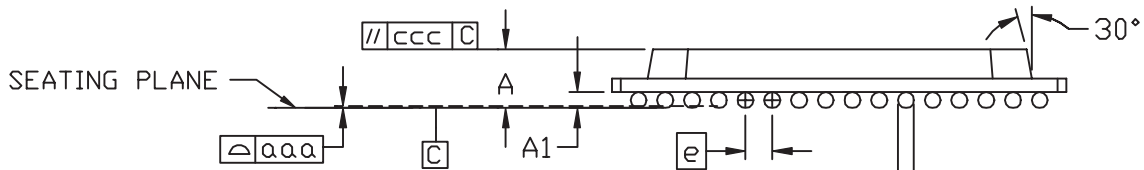
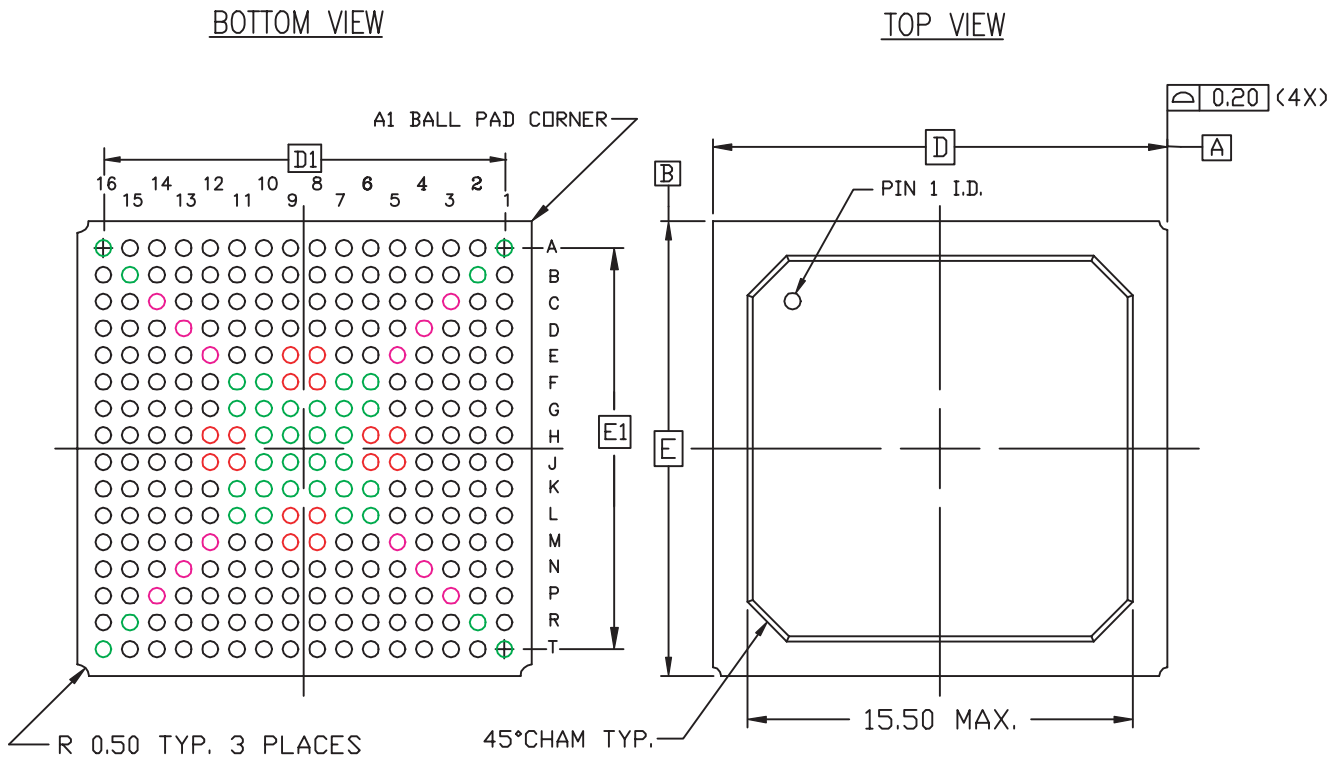
SYMBOL	MILLIMETERS		
	MIN.	NOM.	MAX.
A	---	---	1.20
A1	0.35	0.40	0.45
D/E	12.00 BSC		
D1/E1	9.60 BSC		
e	0.80 BSC		
ϕb	0.45	0.50	0.55
ccc	---	---	0.10
ddd	---	---	0.12
eee	---	---	0.15
fff	---	---	0.08
M	13		

NOTES:

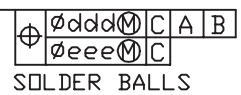
1. ALL DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5M-1994
 2. SYMBOL "M" IS THE PIN MATRIX SIZE.
 3. CONFORMS TO JEDEC MO-205-BE (DEPOPULATED).
- Δ PAD 'E5' IS FOR PAD 'A1' CORNER INDICATION.

Figure 4-31: CS144 Chip-Scale BGA Package

FG256 Fine-Pitch BGA Package (1.00 mm Pitch)



SYMBOL	MILLIMETERS		
	MIN.	NOM.	MAX.
A	$\sqrt{\text{---}}$	1.73	2.00
A ₁	0.40	0.50	0.60
D/E	17.00 BSC		
D ₁ /E ₁	15.00 REF		
e	1.00 BSC		
φb	0.50	0.60	0.70
aaa	$\sqrt{\text{---}}$	$\sqrt{\text{---}}$	0.20
ccc	$\sqrt{\text{---}}$	$\sqrt{\text{---}}$	0.35
ddd	$\sqrt{\text{---}}$	$\sqrt{\text{---}}$	0.30
eee	$\sqrt{\text{---}}$	$\sqrt{\text{---}}$	0.10
M	16		

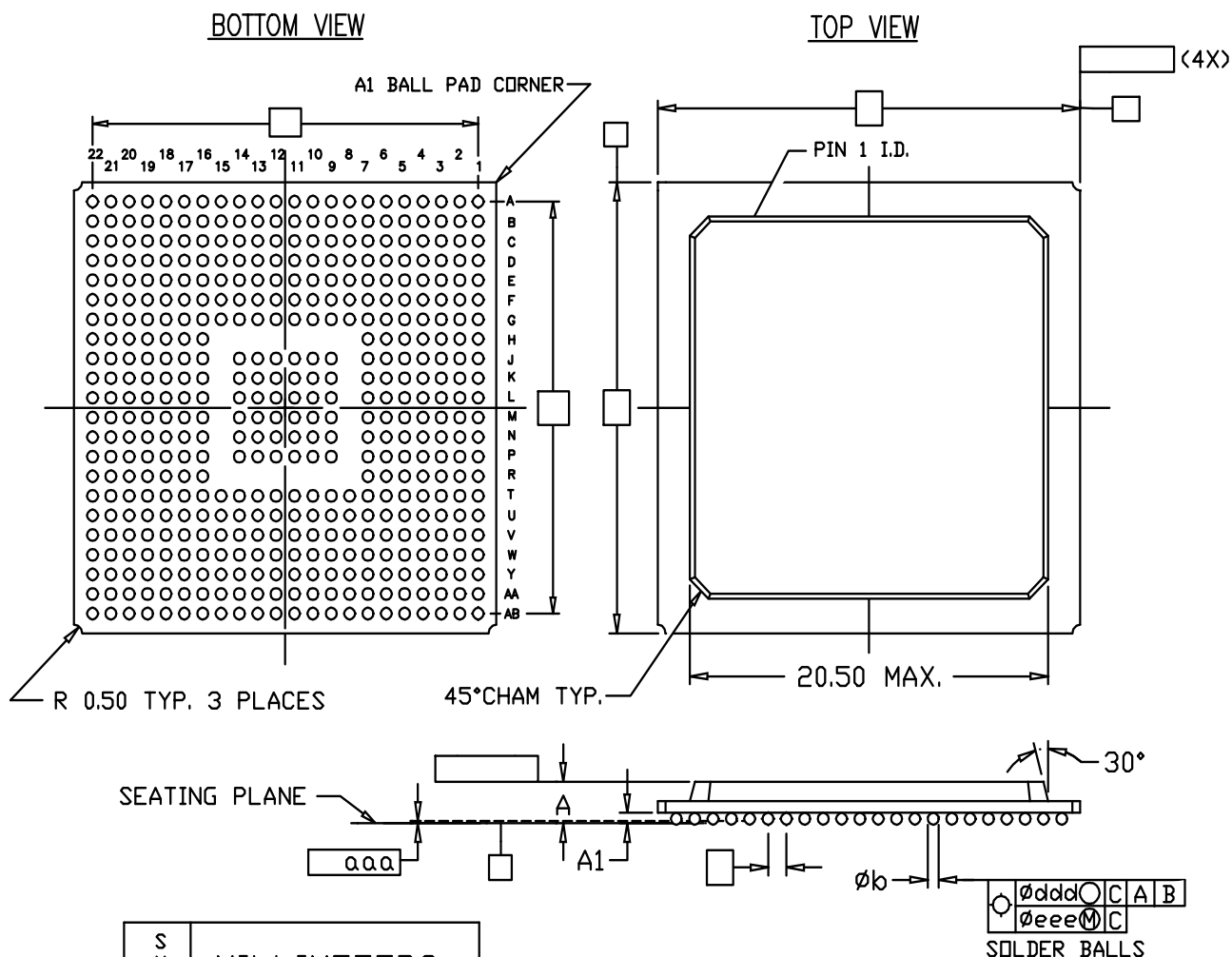


NOTES:

1. ALL DIMENSIONS AND TOLERANCES CONFORM TO ANSI Y14.5M-1994
2. SYMBOL 'M' IS THE BALL MATRIX SIZE.
3. CONFORMS TO JEDEC MO-151 AAF-1.

Figure 4-32: FG256 Fine-Pitch BGA Package

FG456 Fine-Pitch BGA Package (1.00 mm Pitch)



4

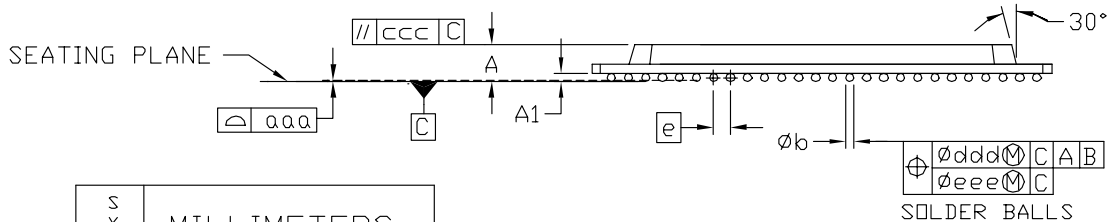
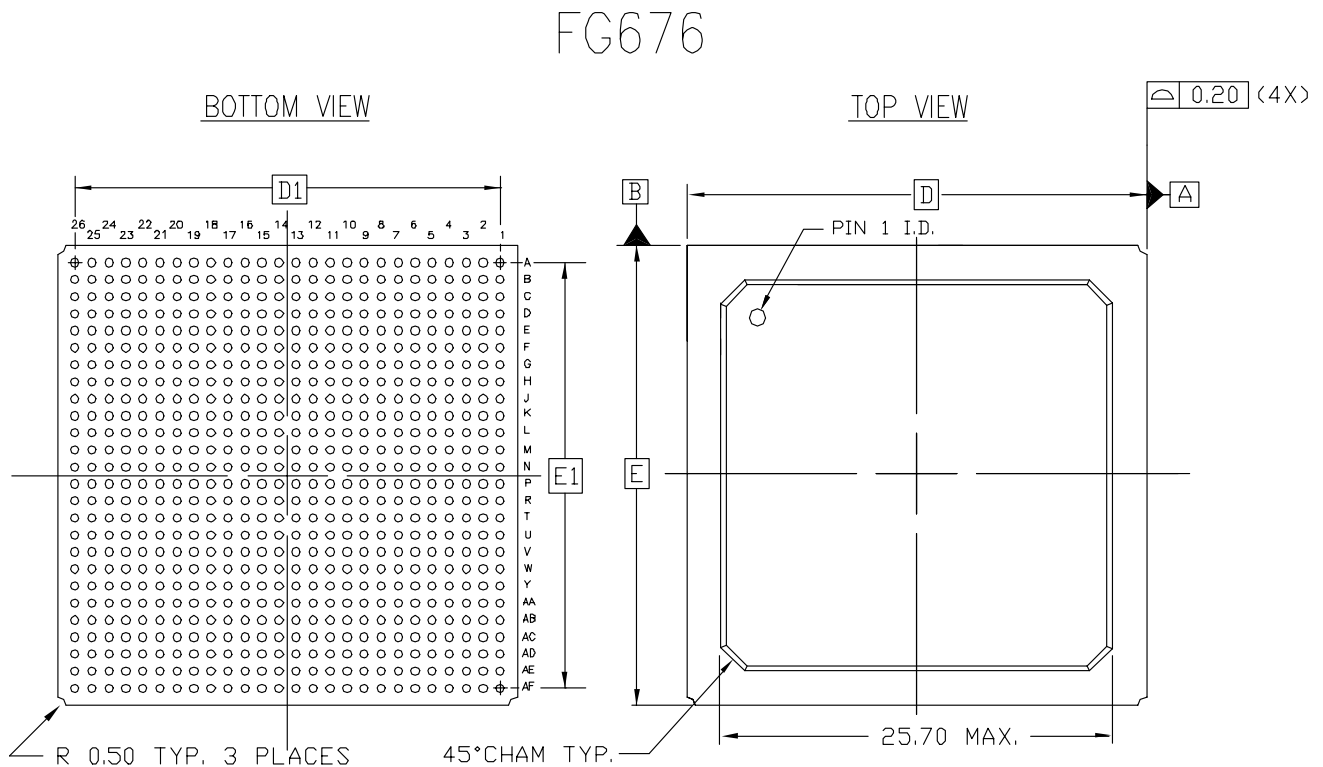
SYMBOL	MILLIMETERS		
	MIN.	NOM.	MAX.
A	\sim	2.20	2.60
A ₁	0.40	0.50	0.60
D/E	23.00 BSC		
D ₁ /E ₁	21.00 REF		
e	1.00 BSC		
øb	0.50	0.60	0.70
aaa	\sim	\sim	0.20
ccc	\sim	\sim	0.35
ddd	\sim	\sim	0.30
eee	\sim	\sim	0.10
M	22		

NOTES:

1. ALL DIMENSIONS AND TOLERANCES CONFORM TO ANSI Y14.5M-1994
2. SYMBOL 'M' IS THE BALL MATRIX SIZE.
3. CONFORMS TO JEDEC MS-034-AAJ-1 (DEPOPULATED)

Figure 4-33: FG456 Fine-Pitch BGA Package

FG676 Fine-Pitch BGA Package (1.00 mm Pitch)



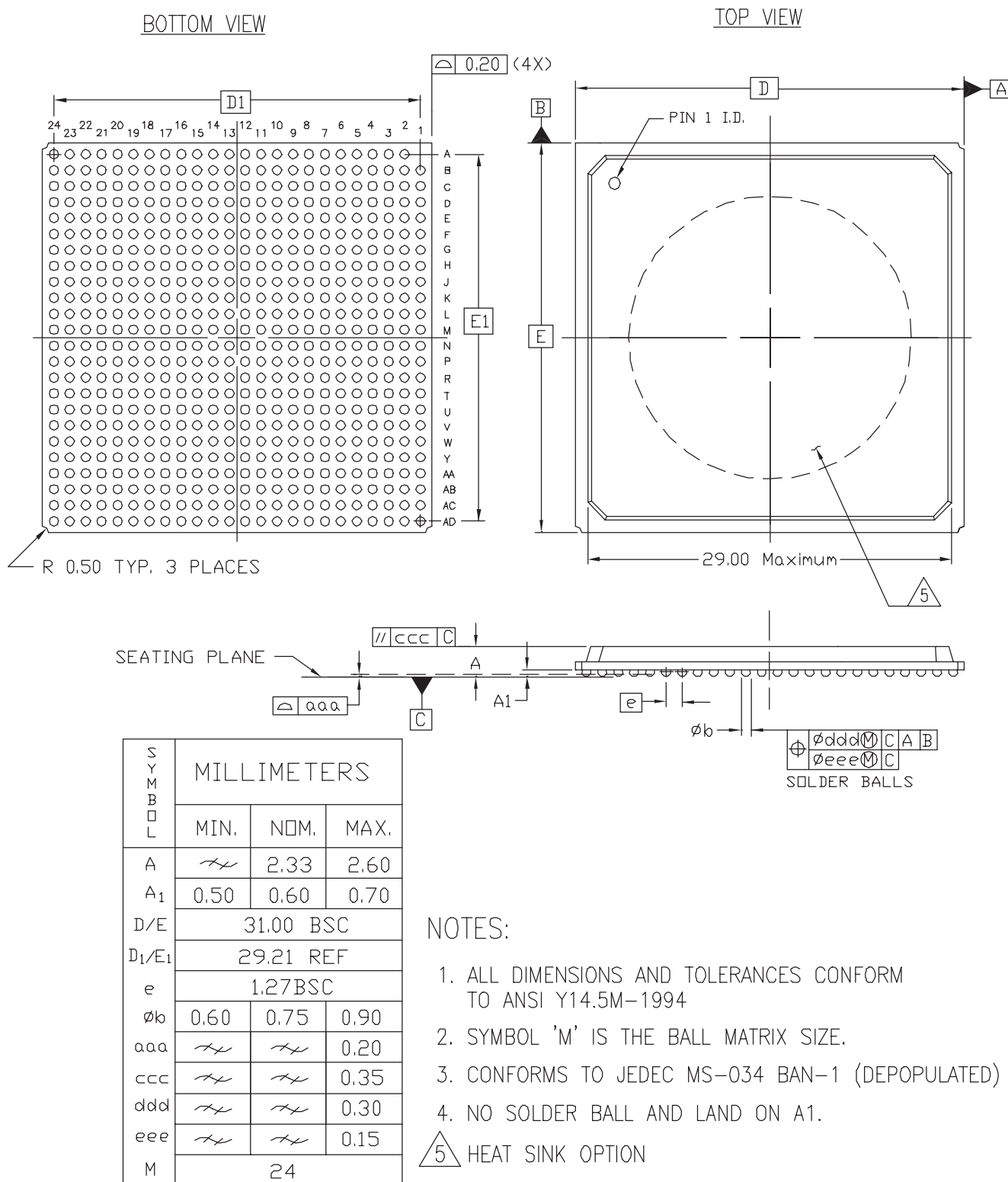
SYMBOL	MILLIMETERS		
	MIN.	NOM.	MAX.
A	$\sqrt{\text{ }}$	2.25	2.60
A ₁	0.40	0.50	0.60
D/E	27.00 BSC		
D ₁ /E ₁	25.00 REF		
e	1.00 BSC		
ϕ_b	0.50	0.60	0.70
aaa	$\sqrt{\text{ }}$	$\sqrt{\text{ }}$	0.20
ccc	$\sqrt{\text{ }}$	$\sqrt{\text{ }}$	0.35
ddd	$\sqrt{\text{ }}$	$\sqrt{\text{ }}$	0.30
eee	$\sqrt{\text{ }}$	$\sqrt{\text{ }}$	0.10
M	26		

NOTES:

1. ALL DIMENSIONS AND TOLERANCES CONFORM TO ANSI Y14.5M-1994
2. SYMBOL 'M' IS THE BALL MATRIX SIZE.
3. CONFORMS TO JEDEC MS-034-AAL-1

Figure 4-34: FG676 Fine-Pitch BGA Package

BG575 Standard BGA Package (1.27 mm Pitch)



4

Figure 4-35: BG575 Standard BGA Package

BG728 Standard BGA Package (1.27 mm Pitch)

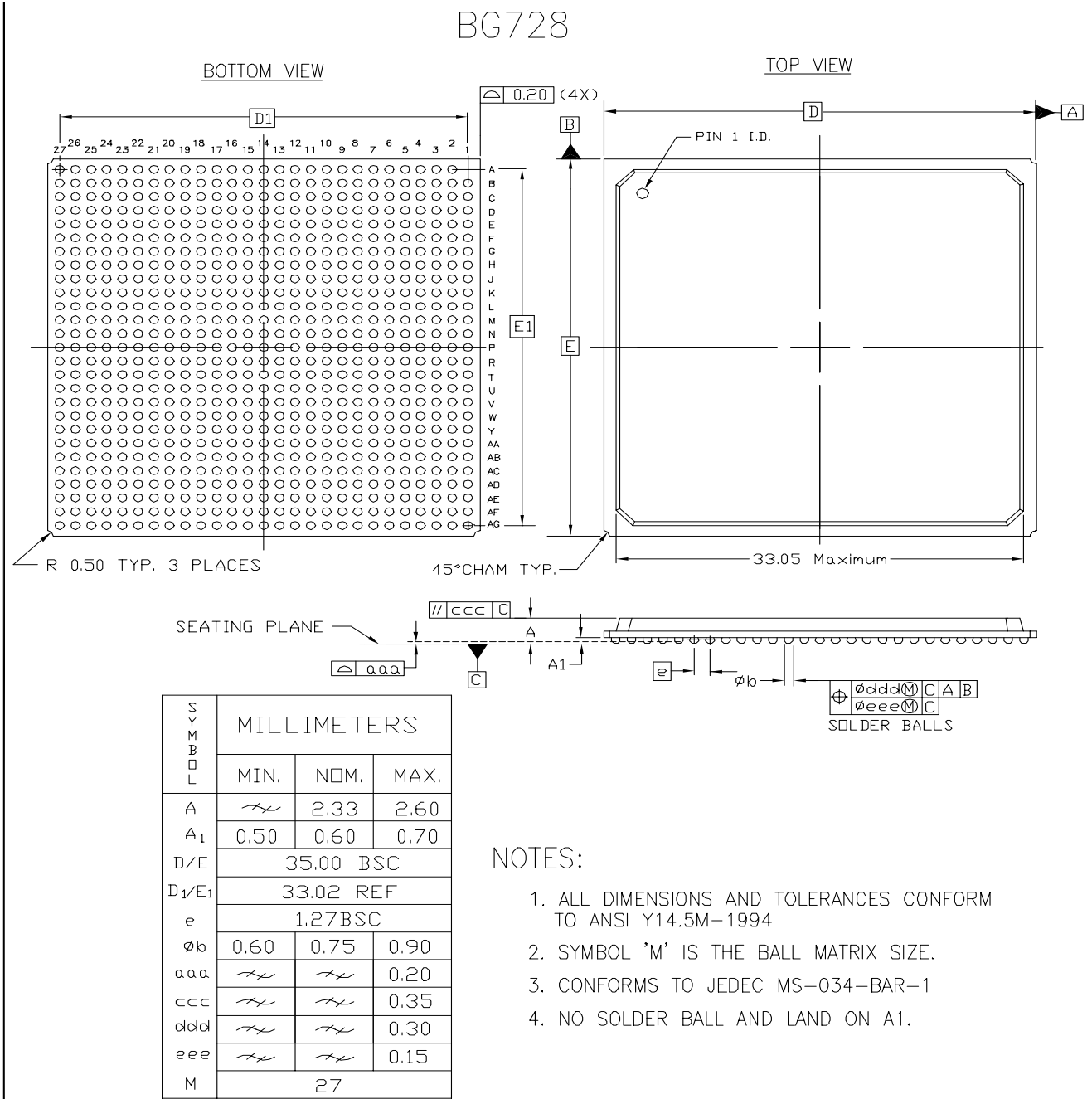


Figure 4-36: BG728 Standard BGA Package

FF896 Flip-Chip Fine-Pitch BGA Package (1.00 mm Pitch)

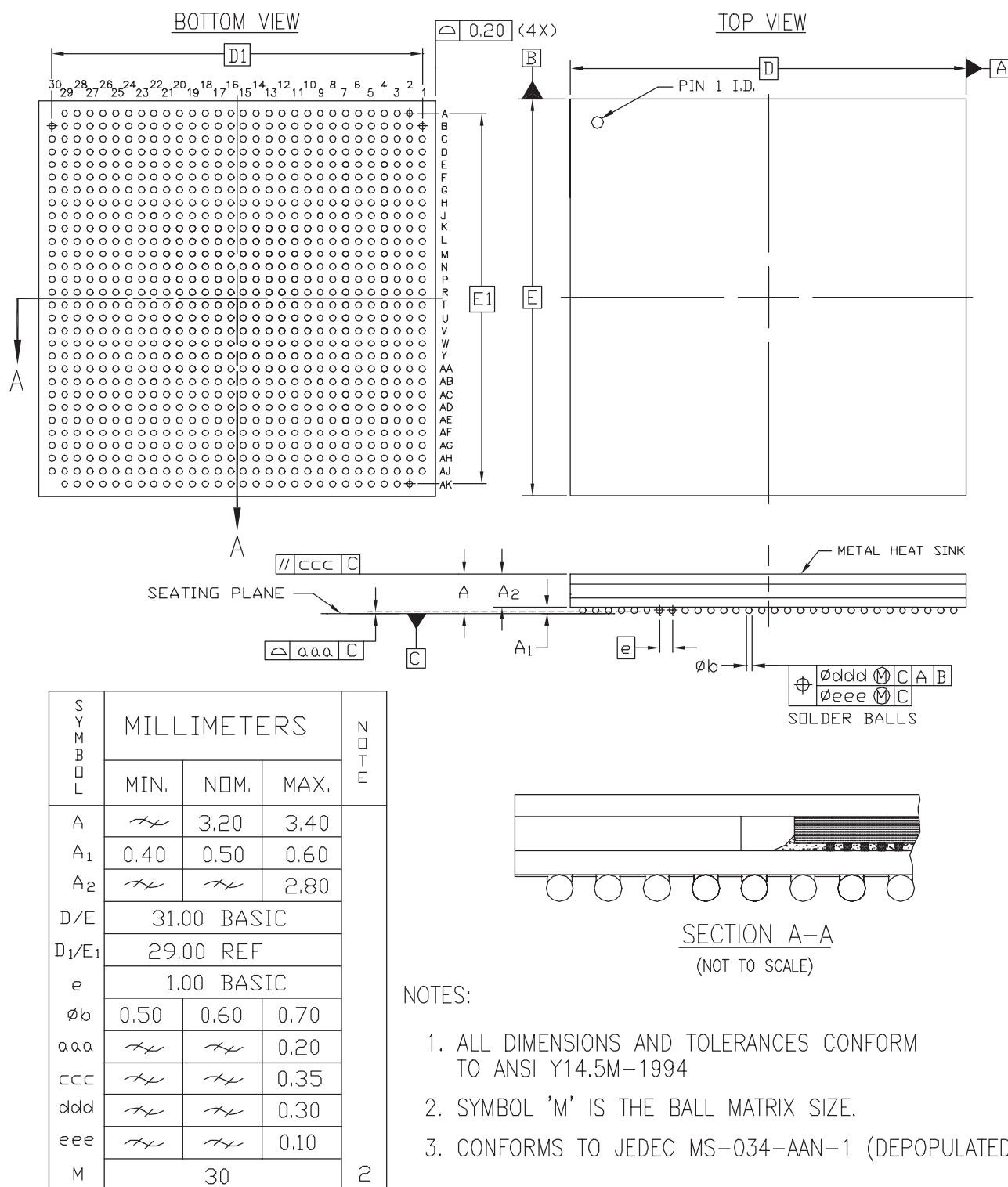


Figure 4-37: FF896 Flip-Chip Fine-Pitch BGA Package

FF1152 Flip-Chip Fine-Pitch BGA Package (1.00 mm Pitch)

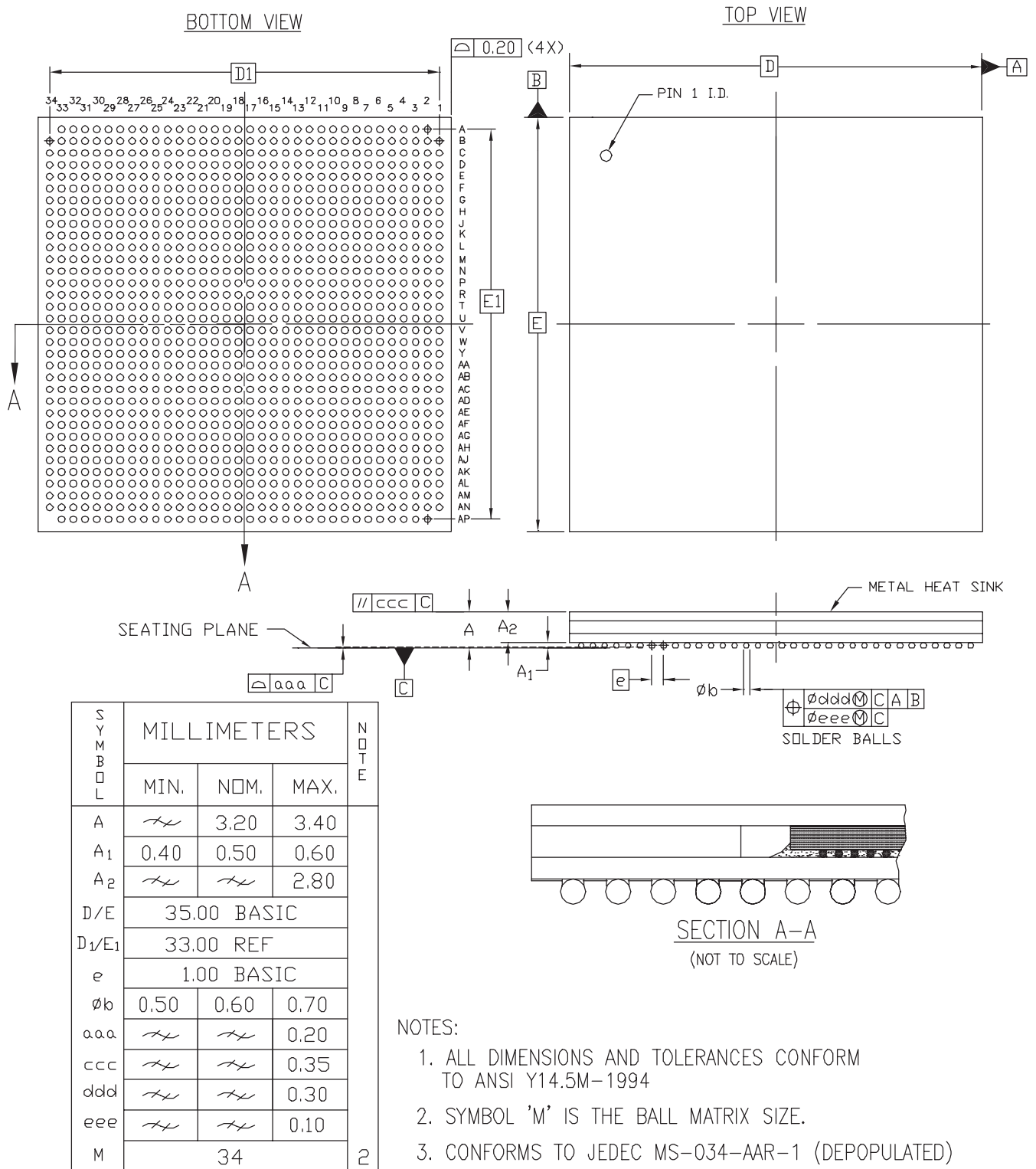


Figure 4-38: FF1152 Flip-Chip Fine-Pitch BGA Package

FF1517 Flip-Chip Fine-Pitch BGA Package (1.00 mm Pitch)

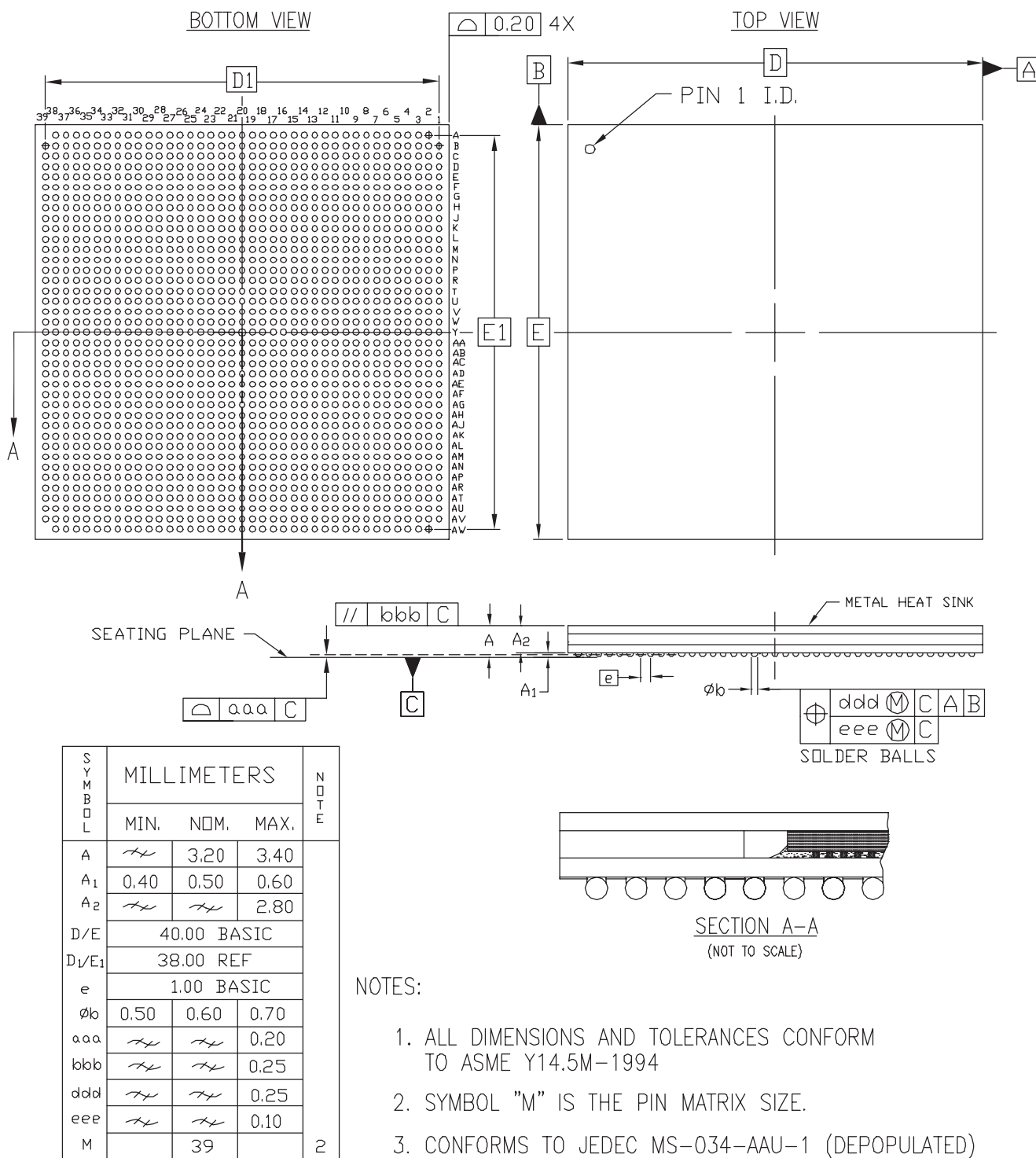


Figure 4-39: FF1517 Flip-Chip Fine-Pitch BGA Package

4

BF957 Flip-Chip BGA Package (1.27 mm Pitch)

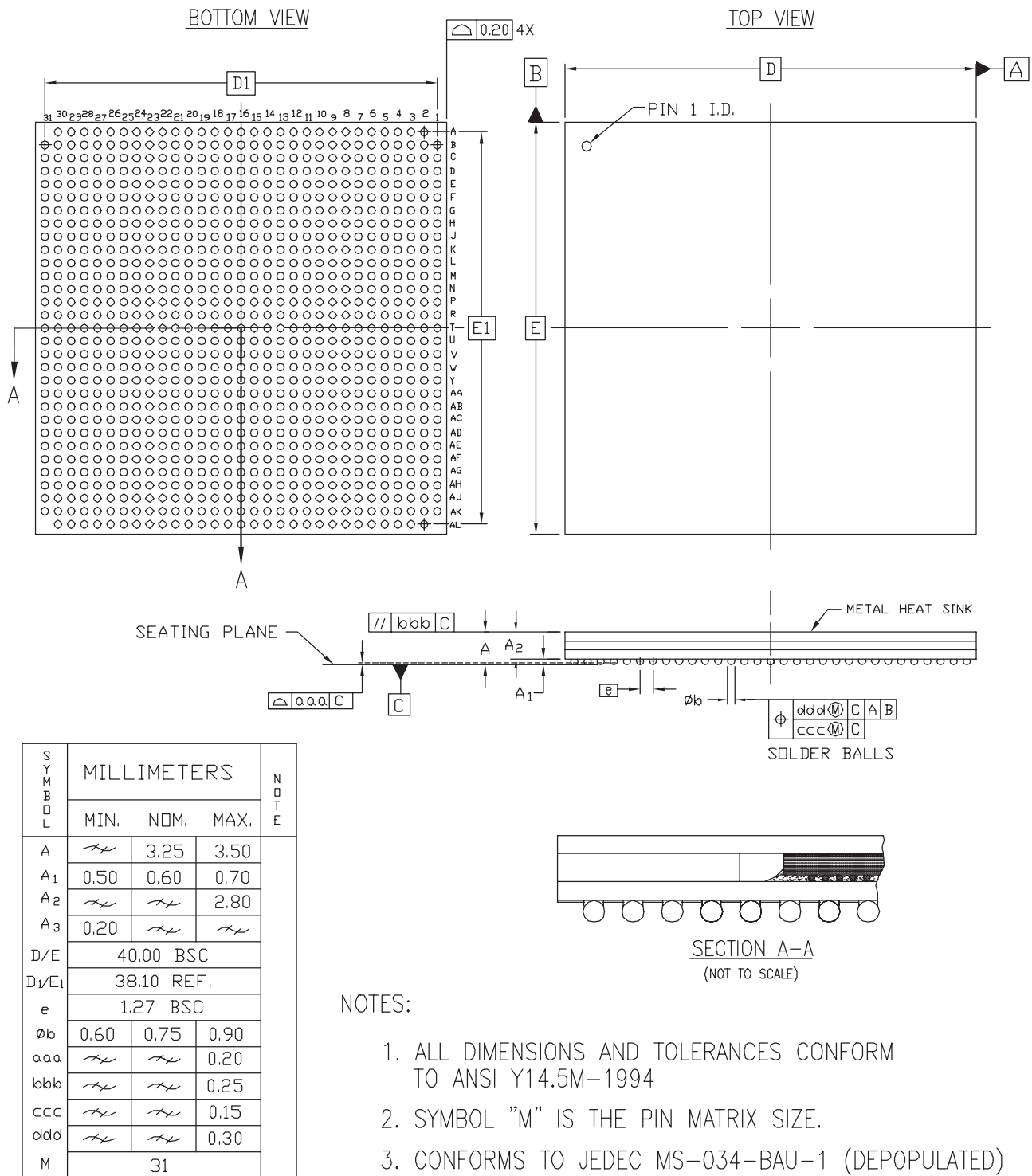


Figure 4-40: BF957 Flip-Chip BGA Package

Flip-Chip Packages

As silicon devices become more integrated with smaller feature sizes as well as increased functionality and performance, packaging technology is also evolving to take advantage of these silicon advancements. Flip-chip packaging is the latest packaging option introduced by Xilinx to meet the demand for high I/O count and high performance required by today's advanced applications.

Flip-chip packaging interconnect technology replaces peripheral bond pads of traditional wire-bond interconnect technology with area array interconnect at the die/substrate interface.

The area array pads contain wettable metallization for solders (either eutectic or high-lead), where a controlled amount of solder is deposited either by plating or screen-printing. These parts are then reflowed to yield bumped dies with relatively uniform solder bumps spread over the surface of the device. Unlike traditional packaging in which the die is attached to the substrate face up and the connection is made by using wire, the bumped die in a flip-chip package is flipped over and placed face down, with the conductive bumps connecting directly to the matching metal pads on the ceramic or organic laminate substrate. The solder material at molten stage is self-aligning and produces good joints even if the chip is placed offset on the substrate.

Flip-chip packages are assembled on high-density, multi-layer ceramic or organic laminate substrates. Since flip-chip bump pads are in area array configuration, very fine lines and geometry on the substrates are required to be able to successfully route the signals from the die to the periphery of the substrates. Multi-layer build-up structures offer this layout flexibility on flip-chip packages, and they provide improvements in power distribution and signal transmission characteristics.

4

Advantages of Flip-Chip Technology

Flip-chip interconnections in combination with the advanced multi-layer laminated substrates provide superior performance over traditional wire-bond packaging. Benefits include:

- Easy access to core power/ground and shorter interconnects, resulting in better electrical performance
- Better noise control since the inductance of flip-chip interconnect is lower
- Excellent thermal performance due to direct heatsinking to backside of the die
- Higher I/O density since bond pads are in area array format
- Smaller size